

# Yunyou Lu

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	600-V Normally Off $\text{SiN}_x/\text{AlGaIn}/\text{GaIn}$ MIS-HEMT With Large Gate Swing and Low Current Collapse. IEEE Electron Device Letters, 2013, 34, 1373-1375.	2.2	223
2	High-Quality Interface in $\text{Al}_2\text{O}_3/\text{GaIn}/\text{GaIn}/\text{AlGaIn}/\text{GaIn}$ MIS Structures With In Situ Pre-Gate Plasma Nitridation. IEEE Electron Device Letters, 2013, 34, 1497-1499.	2.2	160
3	Low On-Resistance Normally-Off GaN Double-Channel Metal-Oxide Semiconductor High-Electron-Mobility Transistor. IEEE Electron Device Letters, 2015, 36, 1287-1290.	2.2	88
4	AC-Capacitance Techniques for Interface Trap Analysis in GaN-Based Buried-Channel MIS-HEMTs. IEEE Transactions on Electron Devices, 2015, 62, 1870-1878.	1.6	79
5	Characterization of VT-instability in enhancement-mode $\text{Al}_2\text{O}_3\text{-AlGaIn}/\text{GaIn}$ MIS-HEMTs. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1397-1400.	0.8	66
6	1.4-kV AlGaIn/GaIn HEMTs on a GaN-on-SOI Platform. IEEE Electron Device Letters, 2013, 34, 357-359.	2.2	53
7	Surface nitridation for improved dielectric/III-nitride interfaces in GaIn MIS-HEMTs. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1059-1065.	0.8	41
8	Enhancement-mode GaN double-channel MOS-HEMT with low on-resistance and robust gate recess. , 2015, , .		38
9	Dynamic Gate Stress-Induced $V_{\text{TH}}$ Shift and Its Impact on Dynamic $R_{\text{ON}}$ in GaIn MIS-HEMTs. IEEE Electron Device Letters, 2016, 37, 157-160.	2.2	36
10	Mapping of interface traps in high-performance $\text{Al}_2\text{O}_3/\text{O}_3/\text{AlGaIn}/\text{GaIn}$ MIS-heterostructures using frequency- and temperature-dependent C-V techniques. , 2013, , .		32
11	Compatibility of $\text{AlN}/\text{SiN}_x$ Passivation With LPCVD- $\text{SiN}_x$ Gate Dielectric in GaIn-Based MIS-HEMT. IEEE Electron Device Letters, 2016, 37, 265-268.	2.2	29
12	High-temperature low-damage gate recess technique and ozone-assisted ALD-grown $\text{Al}_2\text{O}_3/\text{O}_3$ gate dielectric for high-performance normally-off GaIn MIS-HEMTs. , 2014, , .		28
13	Thermally induced threshold voltage instability of III-Nitride MIS-HEMTs and MOS-HEMTs: Underlying mechanisms and optimization schemes. , 2014, , .		28
14	Mechanisms of thermally induced threshold voltage instability in GaIn-based heterojunction transistors. Applied Physics Letters, 2014, 105, .	1.5	19
15	Investigation of $\text{SiN}_x$ and AlN Passivation for AlGaIn/GaIn High-Electron-Mobility Transistors: Role of Interface Traps and Polarization Charges. IEEE Journal of the Electron Devices Society, 2020, 8, 358-364.	1.2	19
16	III-Nitride transistors with photonic-ohmic drain for enhanced dynamic performances. , 2015, , .		18
17	Normally off $\text{Al}_2\text{O}_3/\text{O}_3$ & #x2013; AlGaIn/GaIn MIS-HEMT With Transparent Gate Electrode for Gate Degradation Investigation. IEEE Transactions on Electron Devices, 2015, 62, 821-827.	1.6	18
18	A High-Voltage Low-Standby-Power Startup Circuit Using Monolithically Integrated E/D-Mode AlGaIn/GaIn MIS-HEMTs. IEEE Transactions on Electron Devices, 2014, 61, 762-768.	1.6	16

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19	Characterization of SiN <sub>x</sub> /AlN passivation stack with epitaxial AlN grown on AlGaIn/GaN heterojunctions by plasma-enhanced atomic layer deposition. Applied Physics Express, 2015, 8, 064101.	1.1	16
20	Trapping mechanisms in insulated-gate GaN power devices: Understanding and characterization techniques. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600607.	0.8	10
21	650-V GaN-based MIS-HEMTs using LPCVD-SiN <sub>x</sub> as passivation and gate dielectric. , 2015, , .		8
22	Impact of V <sub>th</sub> shift on Ron in E/D-mode GaN-on-Si power transistors: Role of dynamic stress and gate overdrive. , 2016, , .		7
23	Schottky-on-heterojunction optoelectronic functional devices realized on AlGaIn/GaN-on-Si platform. , 2014, , .		6
24	Normally-off GaN MIS-HEMT with improved thermal stability in DC and dynamic performance. , 2015, , .		4
25	On-chip addressable Schottky-on-heterojunction light-emitting diode arrays on AlGaIn/GaN-on-Si platform. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 365-368.	0.8	4
26	High-voltage enhancement/Depletion-mode AlGaIn/GaN HEMTs on modified SOI substrates. , 2013, , .		1
27	Monolithically integrated 600-V E/D-mode SiN <sub>x</sub> /AlGaIn/GaN MIS-HEMTs and their applications in low-standby-power start-up circuit for switched-mode power supplies. , 2013, , .		1
28	Surface nitridation for improved dielectric/nitride interfaces in GaN MIS-HEMTs (Phys. Status Solidi A) Tj ETQq0,0 0 rgBT <sub>0</sub> /Overlock	0.8	0
29	Nitridation interfacial-layer technology for enhanced stability in GaN-based power devices. , 2015, , .		0
30	Role of shallow surface traps and polarization charges in nitride-based passivation for AlGaIn/GaN heterojunction FET. , 2016, , .		0